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1	0	semiconductor with ((carbon adj doped adj oxide) with silicon)	USPAT; US-PGPUB	2004/10/12 07:07
2	0	((carbon adj doped adj oxide) with silicon)	USPAT; US-PGPUB	2004/10/12 07:07
3	298	(carbon adj doped adj oxide)	USPAT; US-PGPUB	2004/10/12 07:07
4	1		USPAT	2004/10/12 08:15
5	1		USPAT	2004/10/12 08:17
6	1		USPAT	2004/10/12 08:18
7	1		USPAT	2004/10/12 08:18
8	1		USPAT	2004/10/12 08:18
9	1		USPAT	2004/10/12 08:19
10	1		USPAT	2004/10/12 08:20
11	1		USPAT	2004/10/12 08:32
12	1		USPAT	2004/10/12 08:32
13	1		USPAT	2004/10/12 09:13
14	1		USPAT	2004/10/12 09:18
15	1		USPAT	2004/10/12 09:18
16	1		USPAT	2004/10/12 09:23
17	1		USPAT	2004/10/12 09:23

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- (0) semiconductor with ((carbon adj doped adj oxide) with silic
- (298) (carbon adj doped adj oxide)
- (1) "6242351".PN

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Tags:	LSPAT US-PGPUB			
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(carbon adj doped adj oxide)				
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#	U. I. Document ID	Issue Date	Pages	Title	Current GR	Current NR	Retrieval C	Inventor	S	C	P
213	US 6740539 B	20040525	6	Carbon-graded layer for impr	438/99	257/E21.277;		Conti, Richard A. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
214	US 6737728 B	20040518	21	On-chip decoupling capacitor	257/532	257/296;		Block, Bruce A. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
215	US 6737727 B	20040518	22	Electronic structures with red	257/531	257/532;		Gates, Stephen McCon	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
216	US 6737725 B	20040518	14	Multilevel interconnect structu	257/522	257/618;		Grill, Alfred et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
217	US 6737365 B	20040518	10	Forming a porous dielectric la	438/778	257/E21.273;		Kloster, Grant M. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
218	US 6734533 B	20040511	9	Electron-beam treated CDO fi	257/632	438/778		Wong, Lawrence D.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
219	US 6734118 B	20040511	12	Dielectric material treatment	438/795	257/E21.242;		Kloster, Grant M. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
220	US 6734096 B	20040511	10	Fine-pitch device lithography	438/624	438/634;		Dalton, Timothy J. et al	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
221	US 6726996 B	20040427	7	Laminated diffusion barrier	428/446	428/209;		Barth, Edward Paul et a	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
222	US 6719920 B	20040413	7	Slurry for polishing a barrier	252/79.1	252/79.4;		Miller, Anne E.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
223	US 6717265 B	20040406	9	Treatment of low-k dielectric	257/750	257/767		Ingerly, Douglas B. et al	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
224	US 6716771 B	20040406	7	Method for post-CMP conver	438/783	257/E21.241;		Buehler, Mark F. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
225	US 6713873 B	20040330	15	Adhesion between dielectric	257/758	257/753;		O'Loughlin, Jennifer et	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
226	US 6709721 B	20040323	17	Purge heater design and proce	427/569	257/E21.277;		Rocha-Alvarez, Juan C	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
227	US 6703324 B	20040309	12	Mechanically reinforced highl	438/787	257/E21.273;		Wong, Lawrence D.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
228	US 6703317 B	20040309	6	Method to neutralize charge i	438/716	438/710;		Cheng, Yi-Lung et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
229	US 6703250 B	20040309	7	Method of controlling plasma	438/9	216/58;		Chiu, Hsien-Kuang	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
230	US 6703069 B	20040309	5	Under bump metallurgy for le	427/123	257/737;		Moon, Peter K. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
231	US 6699797 B	20040302	12	Method of fabrication of low	438/778	257/E21.273;		Morris, Michael A. et al	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
232	US 6693047 B	20040217	7	Method for recycling semicon	438/770	257/E21.251;		Li, Chih-Cheng et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
233	US 6682989 B	20040127	7	Plating a conductive material	438/454	257/E21.259;		Goodner, Michael D. et	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
234	US 6680262 B	20040120	11	Method of making a semicon	438/780	257/E21.241;		Andideh, Ebrahim et al	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
235	US 6680164 B	20040120	7	Solvent free photoresist strip	430/329	134/1.1		Nguyen, Huong Thanh	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
	US 6677263 B	20040112	8	Stacked device and method for	429/794	257/E21.277;		Yoo, Hyun-Jae et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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(carbon adj doped adj oxide)

U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval C	Inventor	S	C	P	W	E	F	G	H	I	J
234	<input checked="" type="radio"/>	US 6680262 B	20040120	11	Method of making a semicon	438/780	257/E21.241;		Andideh, Ebrahim et al.	<input checked="" type="checkbox"/>									
235	<input checked="" type="radio"/>	US 6680164 B	20040120	7	Solvent free photoresist strip	430/329	134/1.1		Nguyen, Huong Thanh	<input checked="" type="checkbox"/>									
236	<input checked="" type="radio"/>	US 6677253 B	20040113	9	Carbon doped oxide depositi	438/784	257/E21.277;		Andideh, Ebrahim et al	<input checked="" type="checkbox"/>									
237	<input checked="" type="radio"/>	US 6677251 B	20040113	8	Method for forming a hydrop	438/778	438/618;		Lu, Hsin-Hsien et al.	<input checked="" type="checkbox"/>									
238	<input checked="" type="radio"/>	US 6677233 B	20040113	10	Material deposition from a liq	438/658	257/E21.174;		Dubin, Valery M.	<input checked="" type="checkbox"/>									
239	<input checked="" type="radio"/>	US 6674146 B	20040106	7	Composite dielectric layers	257/508	257/41;		Chow, Loren A.	<input checked="" type="checkbox"/>									
240	<input checked="" type="radio"/>	US 6661094 B	20031209	15	Semiconductor device having	257/758	257/751;		Morrow, Patrick et al.	<input checked="" type="checkbox"/>									
241	<input checked="" type="radio"/>	US 6657305 B	20031202	7	Semiconductor recessed mask	257/773			Cohen, Stephen Alan et	<input checked="" type="checkbox"/>									
242	<input checked="" type="radio"/>	US 6653229 B	20031125	9	Integrated circuit with a recess	438/637	257/301;		Cox, J. Neal	<input checked="" type="checkbox"/>									
243	<input checked="" type="radio"/>	US 6649489 B	20031118	8	Poly etching solution to impro	438/424	257/E21.549;		Chang, Li-Wen et al.	<input checked="" type="checkbox"/>									
244	<input checked="" type="radio"/>	US 6638835 B	20031028	12	Method for bonding and debo	438/458	257/E21.568;		Roberds, Brian et al.	<input checked="" type="checkbox"/>									
245	<input checked="" type="radio"/>	US 6638328 B	20031028	9	Bimodal slurry system	51/309	106/3;		Lee, Shen-Nan et al.	<input checked="" type="checkbox"/>									
246	<input checked="" type="radio"/>	US 6635575 B	20031021	38	Methods and apparatus to emb	438/697	134/1.2;		Xia, Li-Qun et al.	<input checked="" type="checkbox"/>									
247	<input checked="" type="radio"/>	US 6630406 B	20031007	10	Plasma ashing process	438/710	257/E21.256;		Waldfried, Carlo et al.	<input checked="" type="checkbox"/>									
248	<input checked="" type="radio"/>	US 6630395 B	20031007	11	Methods for fabricating electri	438/622	438/618;		Kane, Terence Lawrence	<input checked="" type="checkbox"/>									
249	<input checked="" type="radio"/>	US 6630390 B	20031007	8	Method of forming a semicon	438/427	438/435;		Andideh, Ebrahim et al	<input checked="" type="checkbox"/>									
250	<input checked="" type="radio"/>	US 6620741 B	20030916	9	Method for controlling etch bi	438/780	257/40;		Gracias, David H. et al.	<input checked="" type="checkbox"/>									
251	<input checked="" type="radio"/>	US 6610362 B	20030826	4	Method of forming a carbon	427/255.23	427/249.15;		Towle, Steven N.	<input checked="" type="checkbox"/>									
252	<input checked="" type="radio"/>	US 6605549 B	20030812	12	Method for improving nucleat	438/758	438/778;		Leu, Jihperng et al.	<input checked="" type="checkbox"/>									
253	<input checked="" type="radio"/>	US 6602806 B	20030805	39	Thermal CVD process for dep	438/786	257/E21.277;		Xia, Li-Qun et al.	<input checked="" type="checkbox"/>									
254	<input checked="" type="radio"/>	US 6599838 B	20030729	8	Method for forming metal fill	438/692	438/623;		Shih, Tsu et al.	<input checked="" type="checkbox"/>									
255	<input checked="" type="radio"/>	US 6593615 B	20030715	5	Dielectric gap fill process that	257/310	257/347;		Shu, Jen et al.	<input checked="" type="checkbox"/>									
256	<input checked="" type="radio"/>	US 6583497 B	20030624	39	Surface treatment of c-doped	257/642	257/E21.241;		Xia, Li-Qun et al.	<input checked="" type="checkbox"/>									
257	<input checked="" type="radio"/>	US 6570705 B	20030617	6	Method of forming a	438/627	438/627;		Yen, Diana S. et al.	<input checked="" type="checkbox"/>									

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U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XP	Retrieval C	Inventor	S	C	P	Y	Z
266		US 6528116 B	20030304	38	Lid cooling mechanism and m	427/255.37	257/E21.277;		Pokharna, Himansu et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
267		US 6522000 B	20030218	4	Method for making a semicon	257/751	257/345;		Jain, Ajay	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
268		US 6518171 B	20030211	8	Dual damascene process usin	438/624	438/626;		Towle, Steven N.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
269		US 6500755 B	20021231	14	Resist trim process to define s	438/637	438/444;		Dakshina-Murthy, Srik	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
270		US 6486061 B	20021126	39	Post-deposition treatment to e	438/680	257/E21.241;		Xia, Li-Qun et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
271		US 6482754 B	20021119	5	Method of forming a carbon	438/780	257/E21.277;		Andideh, Ebrahim et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
272		US 6479391 B	20021112	21	Method for making a dual da	438/706	257/E21.257;		Morrow, Patrick et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
273		US 6475930 B	20021105	6	UV cure process and tool for	438/787	257/E21.241;		Junker, Kurt H. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
274		US 6465372 B	20021015	39	Surface treatment of C-doped	438/787	257/E21.241;		Xia, Li-Qun et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
275		US 6455426 B	20020924	4	Method for making a semicon	438/687	257/E21.576;		Jain, Ajay	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
276		US 6448185 B	20020910	10	Method for making a semicon	438/706	438/687;		Andideh, Ebrahim et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
277		US 6448177 B	20020910	17	Method of making a semicon	438/638	257/E21.579;		Morrow, Patrick et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
278		US 6441491 B	20020827	16	Ultralow dielectric constant m	257/759	257/E21.261;		Grill, Alfred et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
279		US 6436822 B	20020820	4	Method for making a carbon	438/681	257/E21.261;		Towle, Steven N.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
280		US 6432811 B	20020813	12	Method of forming structural	438/619	257/E21.273;		Wong, Lawrence D.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
281		US 6429117 B	20020806	7	Method to create copper traps	438/627	257/E21.241;		Sudijono, John et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
282		US 6417755 B	20020709	18	Method for fabrication of hig	336/200	29/602.1;		Liu, Q. Z. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
283		US 6417098 B	20020709	8	Enhanced surface modificatio	438/638	257/E21.251;		Wong, Lawrence D. et	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
284		US 6413852 B	20020702	16	Method of forming multilevel	438/619	257/E21.576;		Grill, Alfred et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
285		US 6406993 B	20020618	10	Method of defining small ope	438/624	438/618;		Dakshina-Murthy, Srik	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
286		US 6396122 B	20020528	18	Method for fabricating on-chi	257/531	257/528;		Howard, David et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
287		US 6391783 B	20020521	6	Method to thin down copper	438/700	257/E21.174;		Sudijono, John et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
288		US 6383951 B	20020507	18	Low dielectric constant materi	438/781	257/E21.279;		Li, Weimin	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
289		US 6320013 B	20020507	9	Method for forming interconnect	438/627	257/E21.200;		Guan, Nai	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>